

# **WP4.4 - Design & Development of a New Sensor Characterization System based on TPA-TCT Technique**

AIDAinnova 3<sup>rd</sup> annual meeting, 18.-21. March 2024, Catania  
Veronika Kraus<sup>1</sup>, Michael Moll<sup>2</sup> on behalf of WP4.4.

1) Vienna University of Technology (TU Wien)

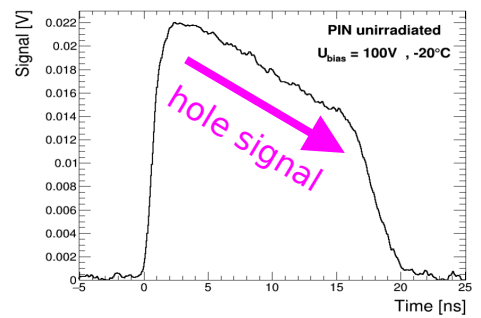
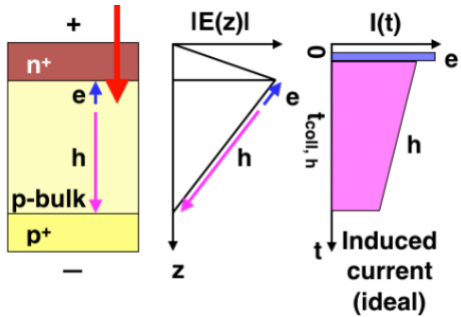
2) CERN



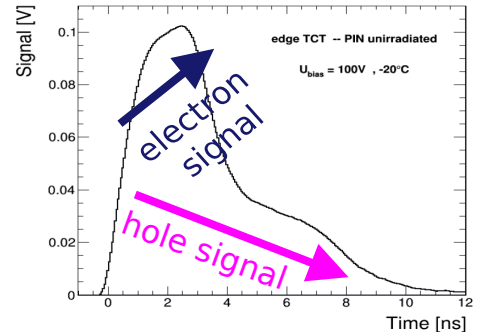
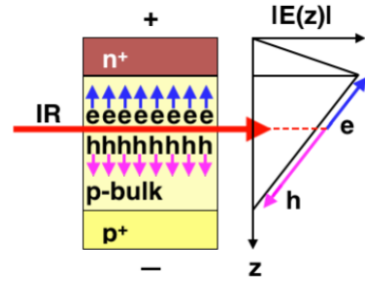
- Brief introduction to TCT and TPA-TCT
- The AIDAinnova TPA-TCT project
  - Examples of recent TPA-TCT applications
  - Measurement technique improvements
- Ongoing developments
  - A new compact TPA-TCT laser system
- Summary and Outlook

- Transient Current Technique (TCT) for characterizing silicon sensors: pulsed laser induces generation of charge carriers
- Illumination with laser light pulse ( $<1\text{ns}$ )  $\rightarrow$  recording the resulting current transient

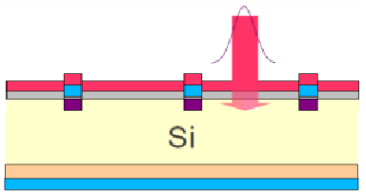
**Example 1:**  
mode: "top TCT"  
  
red laser  
(e.g. 660nm)



**Example 2:**  
mode: "edge TCT"  
  
infrared laser  
(e.g. 1060nm)

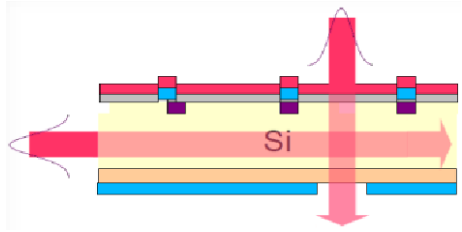


## TCT (red light)



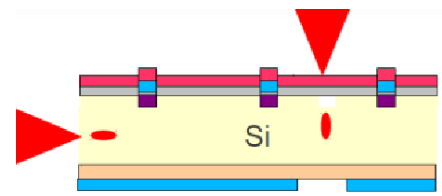
- Short penetration length (650nm = 1.9eV)
- Carriers deposited in a few  $\mu\text{m}$  from surface
- Front & back TCT: study electron & hole drift separately
- 2D spatial resolution (5-10 $\mu\text{m}$ )

## TCT (infrared light)

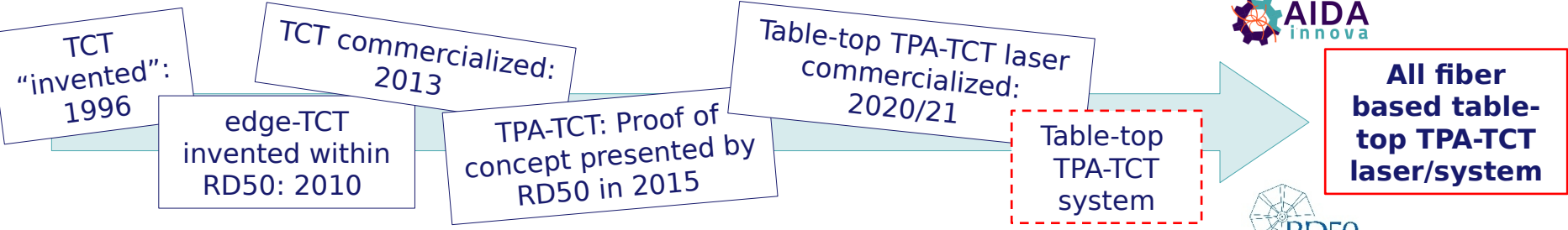


- Long penetration (1064nm = 1.17eV)
- Similar to MIPs (though different  $dE/dx$ )
- Top and edge TCT
- 2D spatial resolution (5-10 $\mu\text{m}$ )

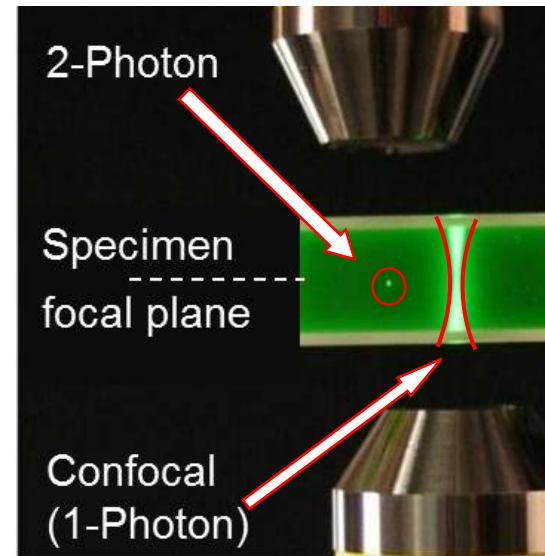
## TPA-TCT (far infrared)



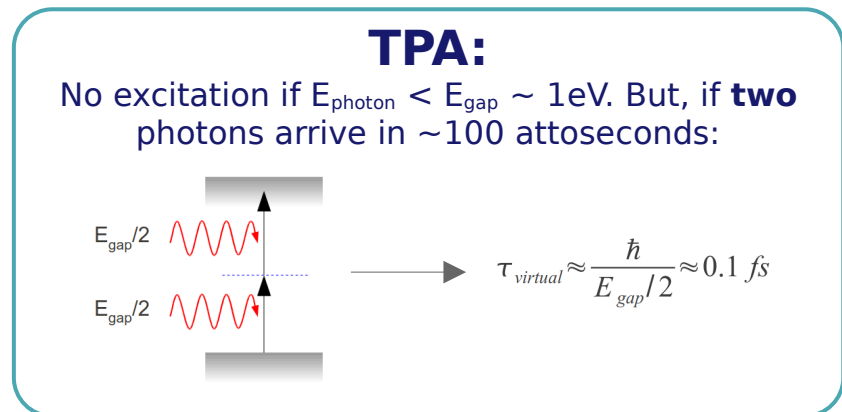
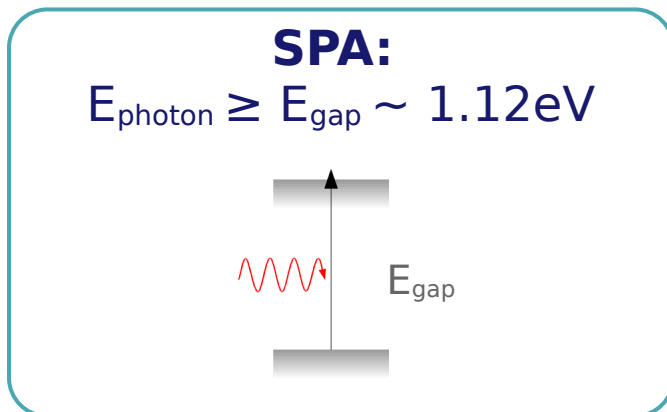
- No single photon absorption in silicon (1550nm = 0.8eV)
- 2 photons produce one electron-hole pair
- Point-like energy deposition in focal point
- **3D** spatial resolution (1 x 1 x 10 $\mu\text{m}$ )



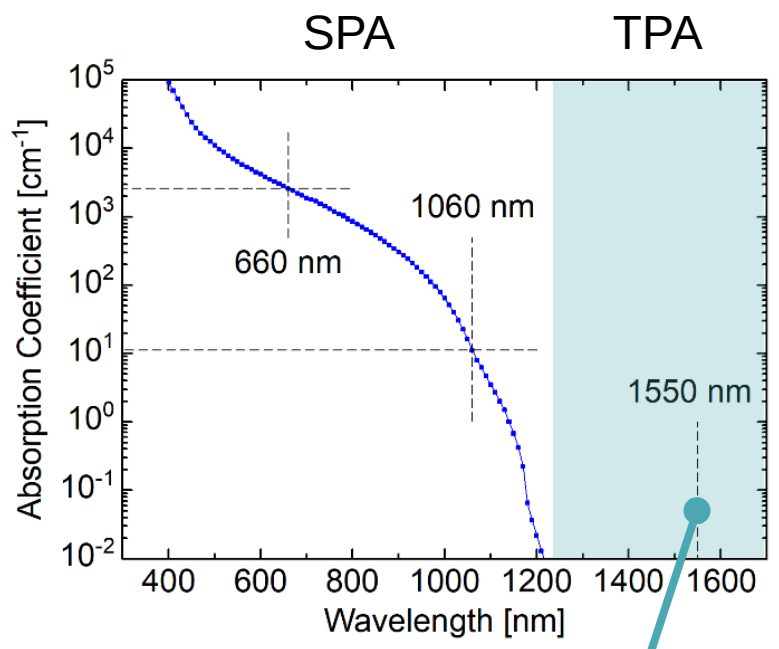
- TCT: Single Photon Absorption (SPA) – continuous energy deposition along beam
- TPA-TCT: Two Photon Absorption (TPA) – absorption only in focal point
- Energy of each photon ( $\lambda=1550\text{nm}$ ) is smaller than the bandgap (individually they can not create an e-h pair), two photons needed to create an e-h pair



[Photo: C. Yanez, Uni of Central Florida]

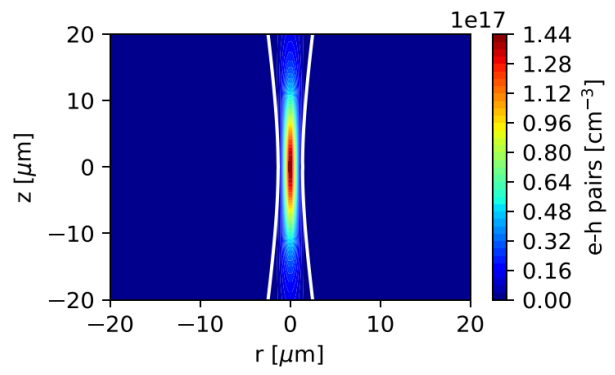


- SPA: Probability to create an e-h pair is proportional to  $\propto I$
- TPA: 2 photons are needed, the probability is  $\propto I^2$

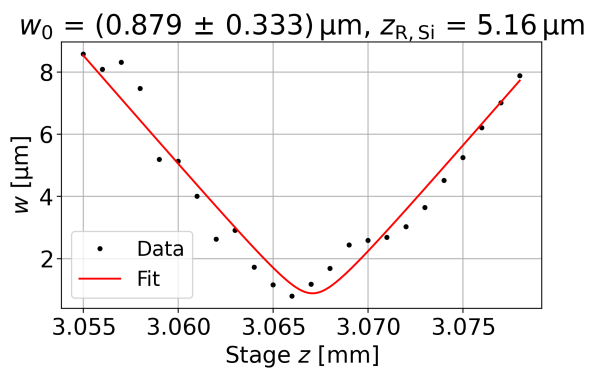


$$\frac{dI(r, z)}{dt} = -\alpha I - \beta I^2(r, z)$$

Simulation of TPA charge carrier density,  $\lambda=1550\text{nm}$



Measurement: Beam waist < 1μm, z<sub>r</sub> ~ 5μm



S. Pape, 38th RD50 workshop

- **Since 2015:** TPA-TCT measurements performed at laser facility (in Bilbao)
  - Proof of concept, demonstration of 3D resolution and feasibility to study irradiated sensors
- **2017:** CERN KT-fund approves & funds a project to develop a table-top TPA-TCT system
  - **2017-18:** development of specs, discussions with laser experts, market survey, ...
    - 03/2018: Call for Tender
    - 06/2018: Order to Fyla
    - **04/2019:** 1<sup>st</sup> prototype arrived at CERN, installation problem & transport damage
    - 07/2019: 2<sup>nd</sup> delivery; installation successful, commissioning, system debugging, ...
    - 10/2019: power cut damages laser, repair
    - 12/2019: replacements of components
    - 07/2020: power stability issues detected, laser returned to FYLA, upgraded
    - **01/2021:** new generation prototype delivered to CERN; since then: data taking
- **AIDAinnova WP4.4.:** further improvements & user community system development & all fiber laser system

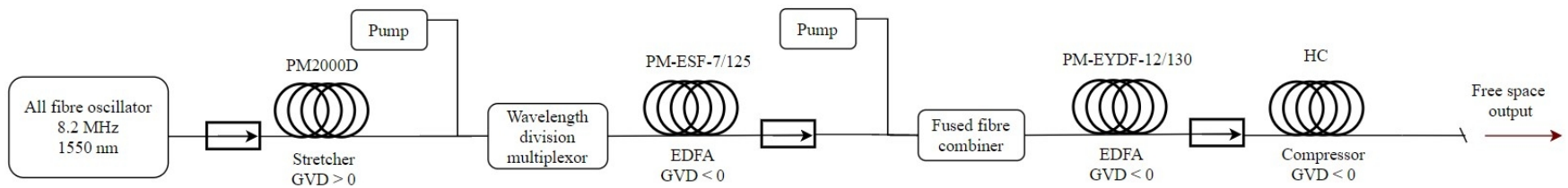
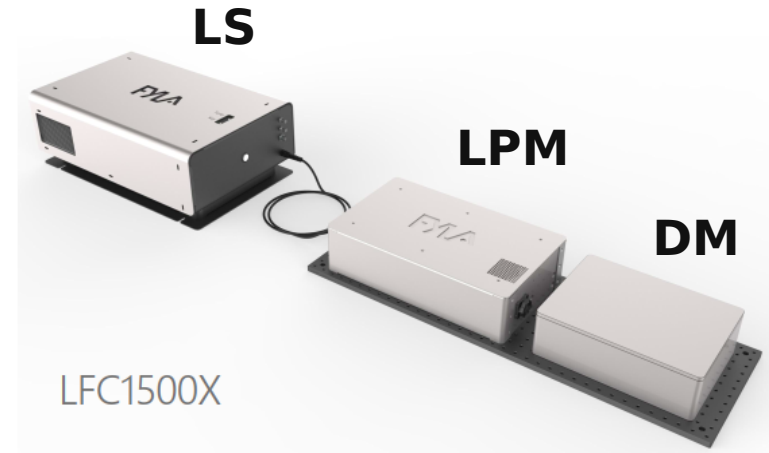


Development of  
FYLA LFC1500X



## Modular femtosecond laser system:

- Laser Source (LS)
  - 10MHz, 1550nm, 300fs
- Laser Pulse Management (LPM)
  - 10pj - 10nj, 10MHz to single shot
- Dispersion management (DM)
  - 300 - 600fs, pulse characterization



Details:

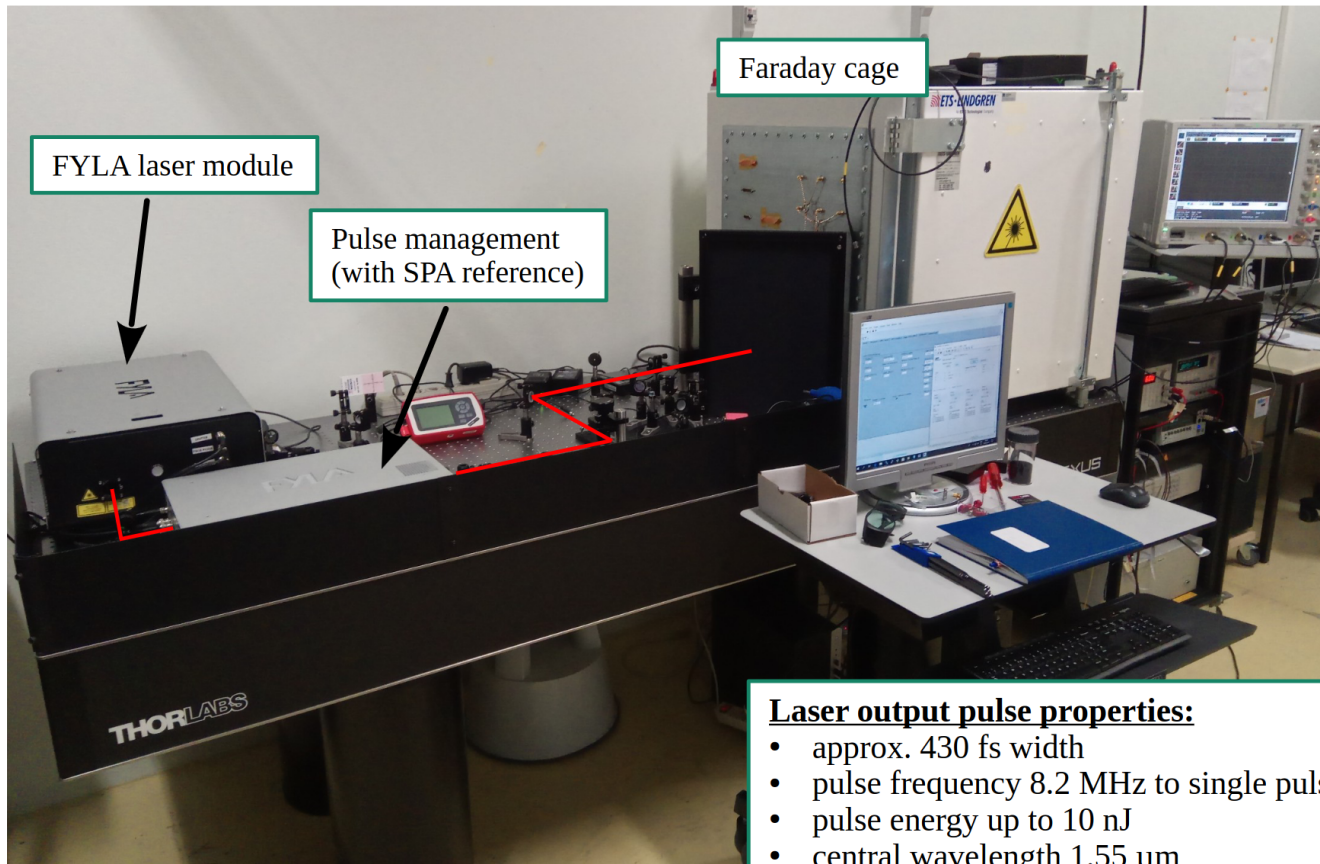
**Fiber Laser System of 1550 nm Femtosecond Pulses with Configurable Properties for the Two-Photon Excitation of Transient Currents in Semiconductor Detectors;** Azahara Almagro-Ruiz, Sebastian Pape, Hector Muñoz, Moritz Wiehe, Esteban Curras Rivera, Marcos Fernández-García, Michael Moll, Raúl Montero Santos, Rogelio Palomo, Cristian Quintana, Iván Vila Álvarez, Pere Pérez-Millán; Applied Optics 61, 9386-9397 (2022); <https://doi.org/10.1364/AO.470780>



- **CERN:** TPA-TCT at the Solid State Detectors (SSD) lab of the EP-DT group (Laser laboratory with interlocked access and personal protection equipment)

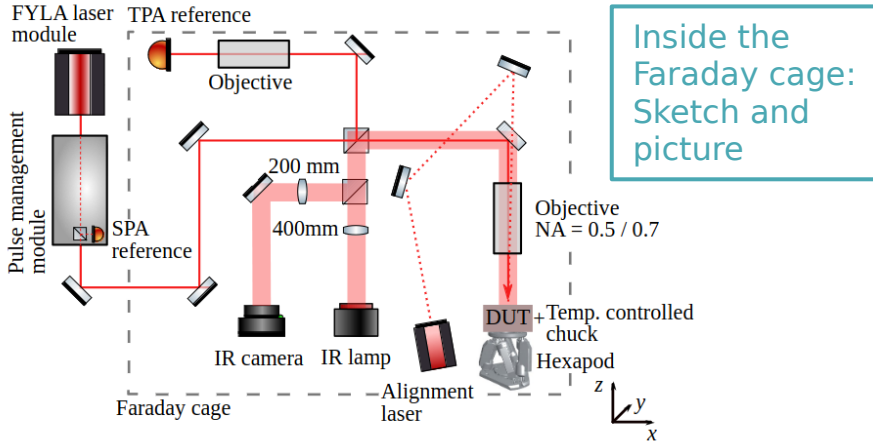


[M. Wiehe et al.: Development of a Tabletop Setup for the Transient Current Technique using Two-Photon Absorption in Silicon Particle Detectors, IEEE TNS, Vol.68, Issue-2, Feb.2021, pages 220-228]



**Laser output pulse properties:**

- approx. 430 fs width
- pulse frequency 8.2 MHz to single pulse
- pulse energy up to 10 nJ
- central wavelength 1.55  $\mu\text{m}$



## Calibration against MIP (<sup>90</sup>Sr):

- Pulse energy against generated charge (285µm PIN; NA = 0.5 at 20°C and 0% humidity)
- The pulse energy is measured with a S401C thermal power sensor from Thorlabs.

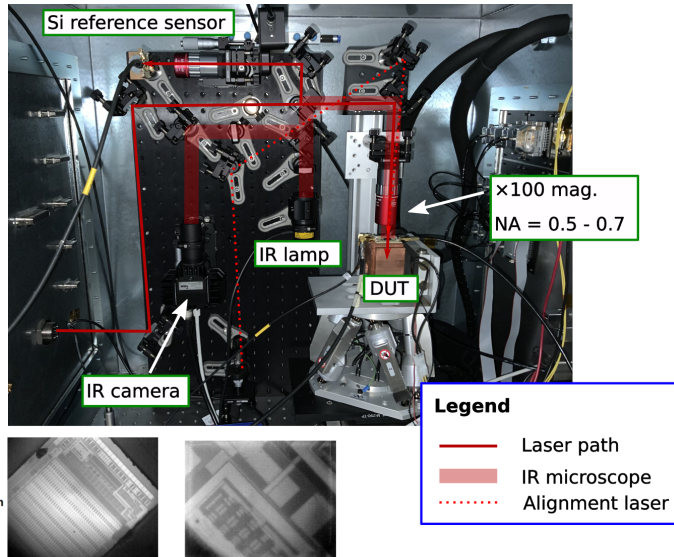
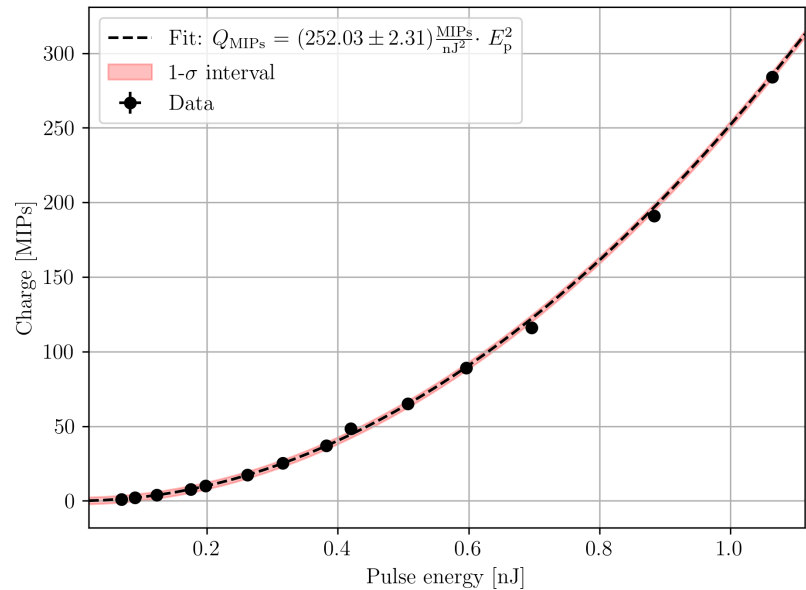
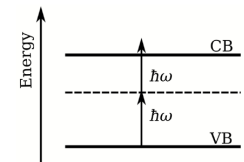


image from rear through bulk

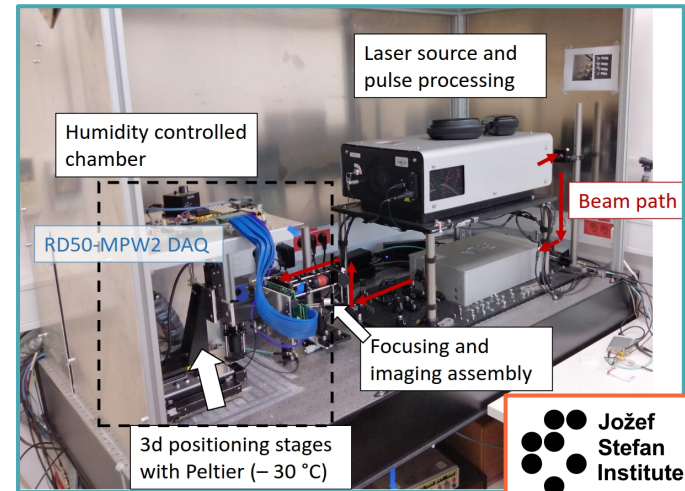
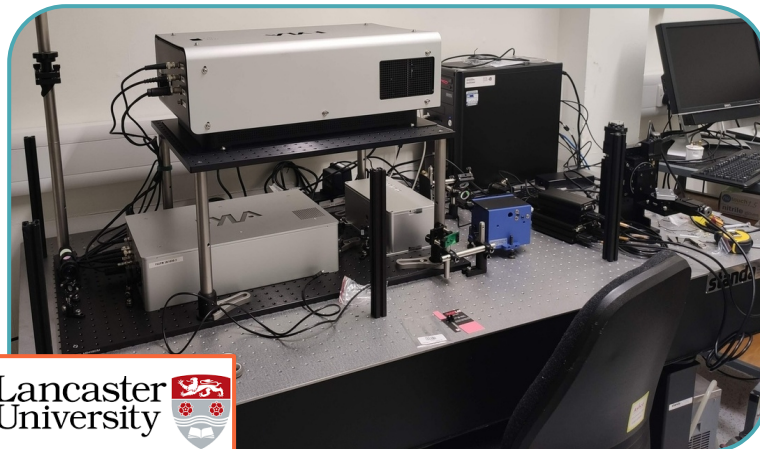
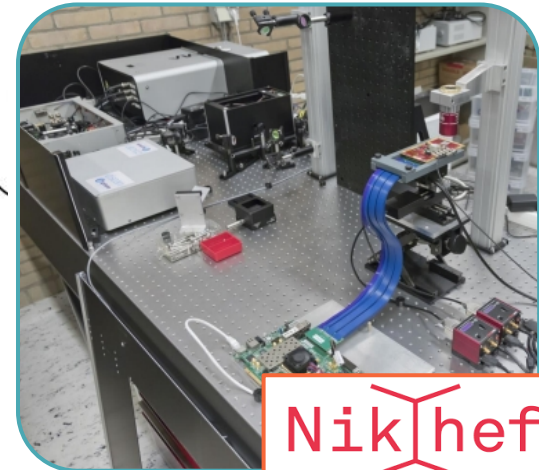
$$\frac{dI(r, z)}{dt} = -\alpha I - \beta I^2(r, z)$$



TPA-TCT systems with the LFC1500X or new "Pulsar" laser system at several institutes:



(In setup phase)



# **Examples of recent TPA-TCT applications & Measurement technique improvements**

- Charge generation decreases with temperature
  - Less phonons available
  - Increasing band gap ( $\sim 1\text{meV}$ )
  - Change in refractive index:  
 $n(-23^\circ\text{C})/n(20^\circ\text{C}) = 99.8\%$   
 $\rightarrow$  negligible

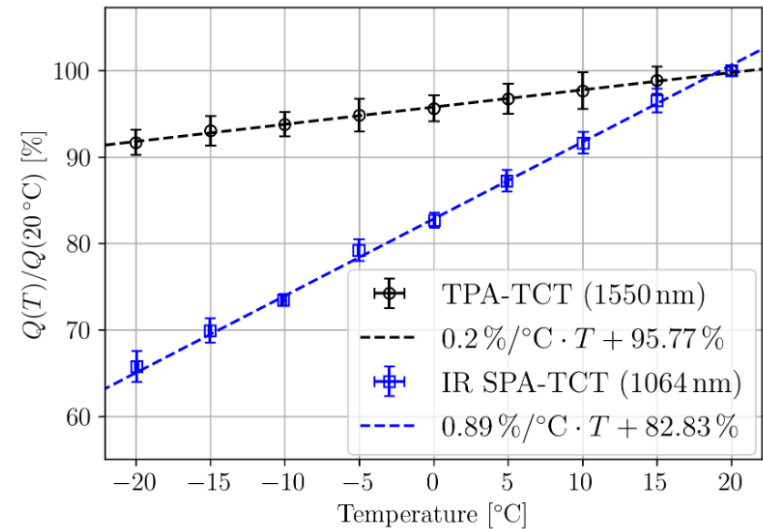
- Dependence is sensitive to wavelength

- Charge generation is given by:

$$Q_{TPA}(T) \sim n_{Si}(T) \beta_2(T)$$

$$Q_{SPA}(T) \sim (1 - \exp(-\alpha(T) \cdot d))$$

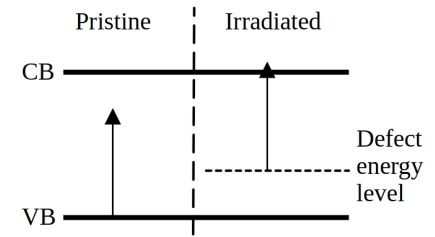
- Temperature dependence is relevant for measurements of irradiated samples (measured at  $-20^\circ\text{C}$  to decrease the leakage current)



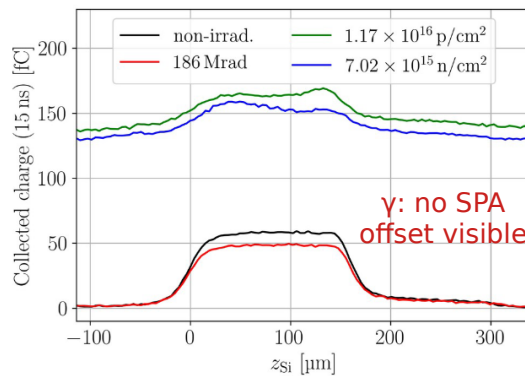
Charge collection efficiency measured with SPA- and TPA-TCT at different temperatures.

Influence of temperature on measurements of the Two Photon Absorption - Transient Current Technique in silicon planar detectors using a 1550 nm femtosecond fibre laser; S. Pape et al., 2023, <https://doi.org/10.1016/j.nima.2023.168387>

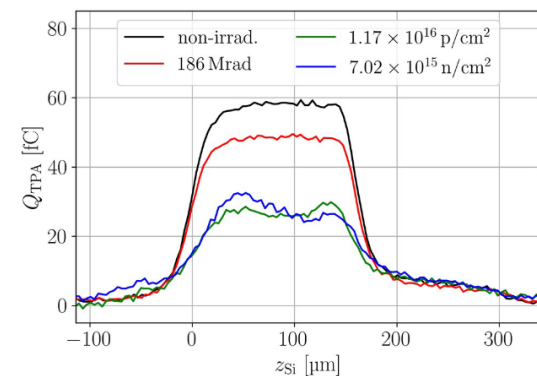
- Radiation damage can introduce new energy levels in the band gap that trap charge carriers
- Trapped charge carriers can be excited by a single 1550nm photon
- This enables a parasitic single photon absorption component to the TPA-TCT measurement (SPA component is found as a offset, as it is not depth dependent  $Q_{SPA}(z) = \text{const.}$ )



Systematic study of influence of radiation damage on the TPA-TCT  
→ n, p, γ



SPA corrected

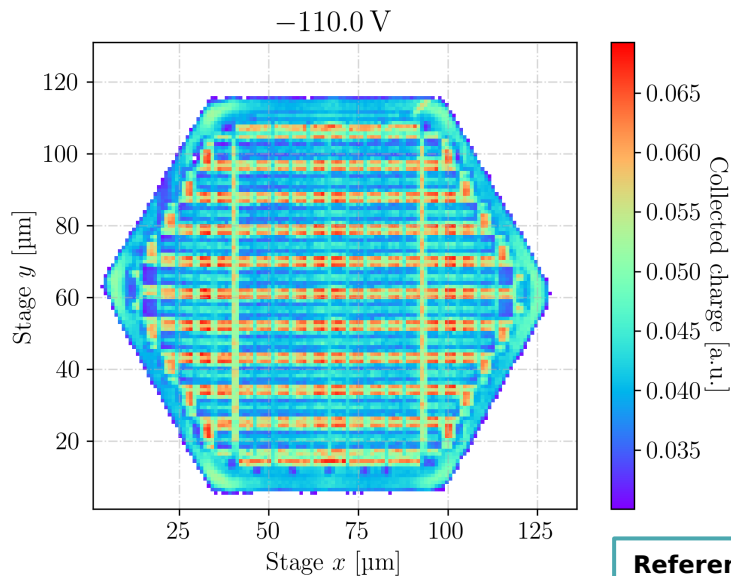


Plot from S. Pape Thesis (2024)

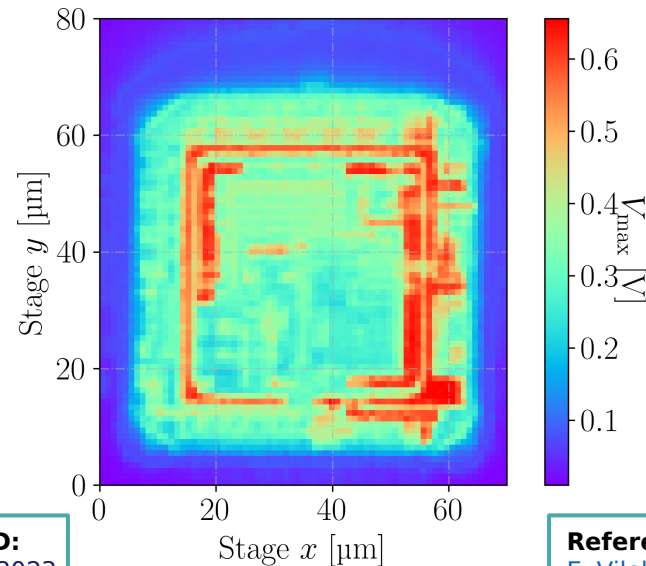
- Increasing hadron irradiation increases the SPA background, γ does not
- **SPA background probably related to NIEL!**

S. Pape, 43rd RD50 workshop

- The examples show the probing of the top side metals of monolithic detectors. Regions with metal have an increased charge collection due to reflection.
- Features in the  $\mu\text{m}$  scale are well resolved ( $\sim 60 \times 60 \mu\text{m}^2$  pixels)!



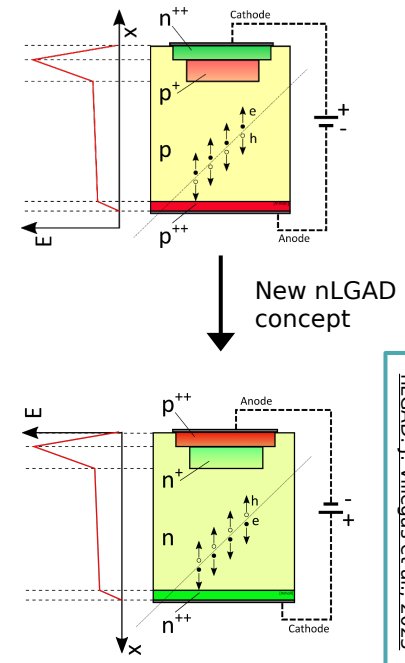
**Reference PicoAD:**  
[M. Milanesio et al. 2023](#)  
[R.Cardella et al. 2022](#)



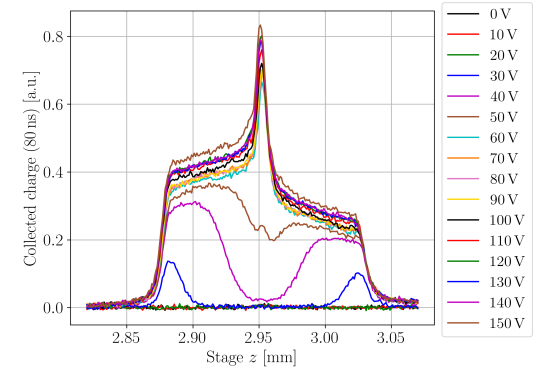
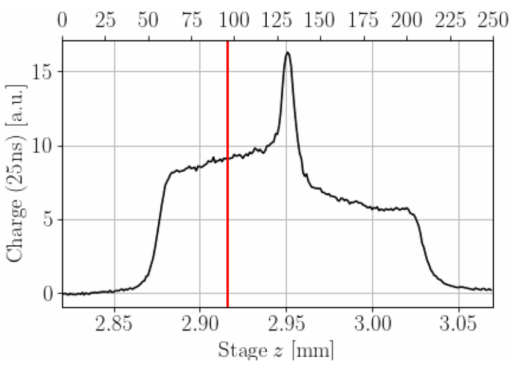
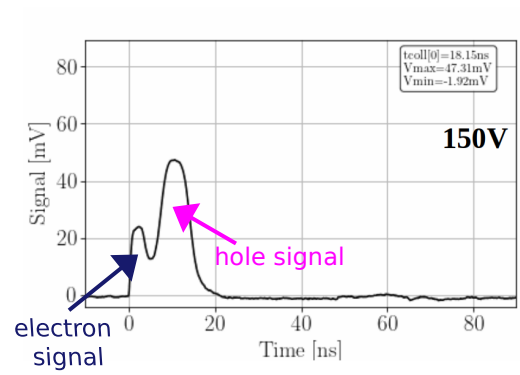
**Reference MPW2:**  
[E. Vilella 2022](#)



- Low Gain Avalanche Detectors (LGAD), implemented as  $n^{++}-p^+-p$ , show outstanding performance when detecting high-energy charged particles
- Due to the difference in multiplication mechanism for holes and electrons, the detection performance for low penetrating particles (e.g low-energy protons or soft x-rays) is significantly reduced
- A novel design of an LGAD detector, the nLGAD, was designed and fabricated at CNM and first tested at CERN with the TPA-TCT

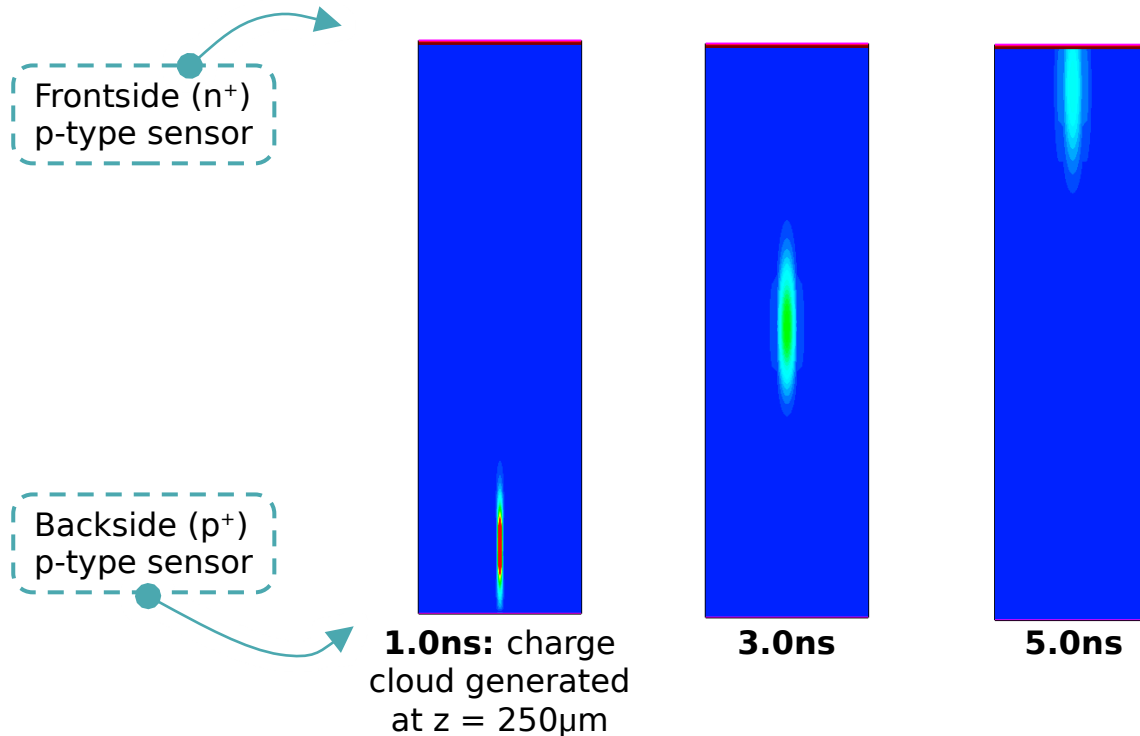


nLGAD: J. Villegas et al., 2023

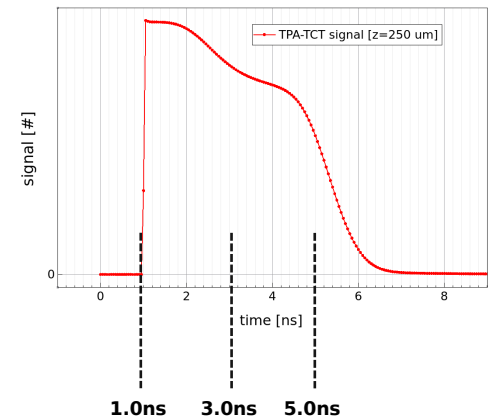




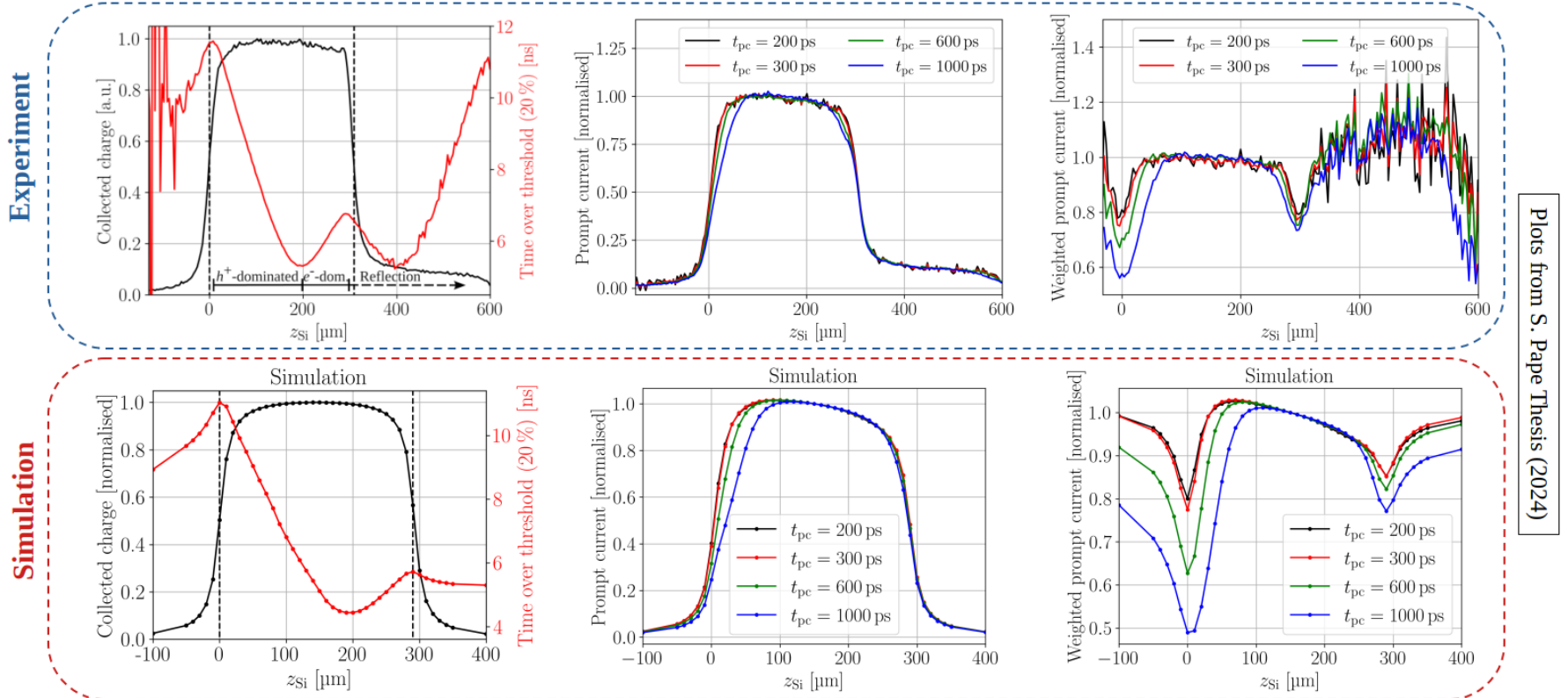
- Simulation of TPA-TCT
  - Charge cloud generated around focal depth of  $250\mu\text{m}$  at  $t=1\text{ns}$
  - Visualisation of electron cloud moving through PIN detector (holes not shown)



**Transient Current (TC)**  
induced by electrons and holes



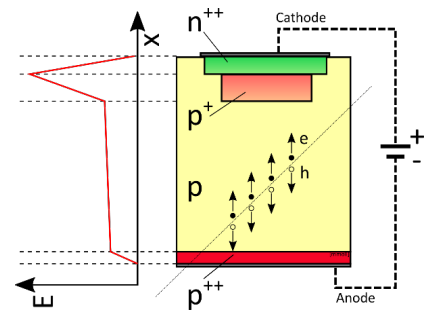
- Comparison of data extracted from experimental current transients versus data extracted from simulated transients taken on a 300 $\mu\text{m}$  thick PIN sensor



Plots from S. Pape Thesis (2024)

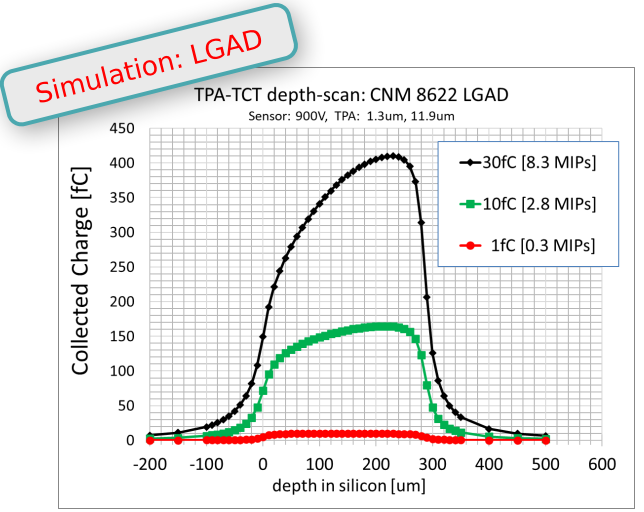
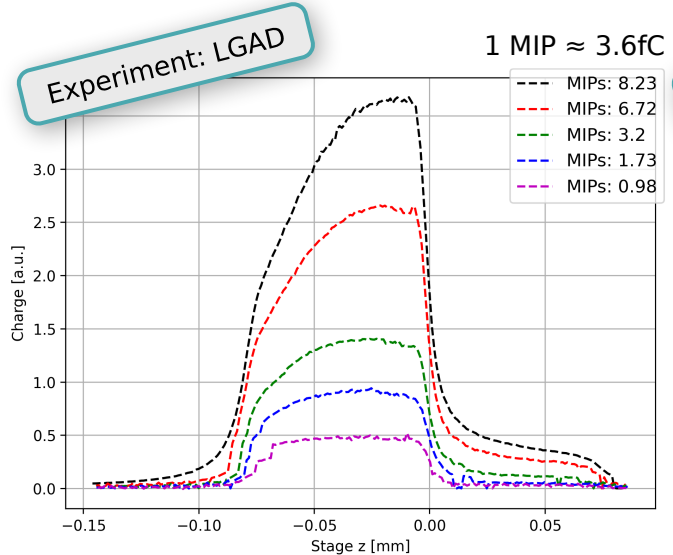
- Gain suppression in LGADs:

- The gain in Low Gain Avalanche Diodes (LGADs) depends on the charge density entering the Gain Layer (GL)
- Low charge density** in GL: negligible gain suppression
- High charge density** in GL: drop in the E-field (less amplification) → reduction in the gain
- Effect relevant for characterization and operation of LGADs for the HL-LHC ATLAS/CMS timing experiments

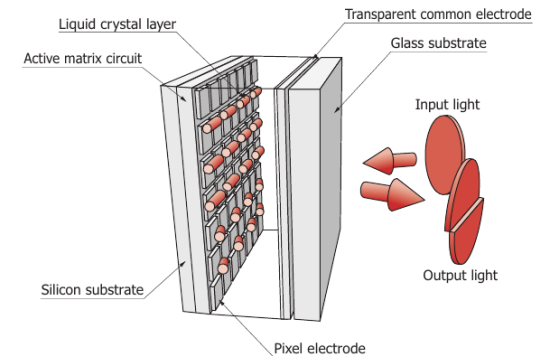
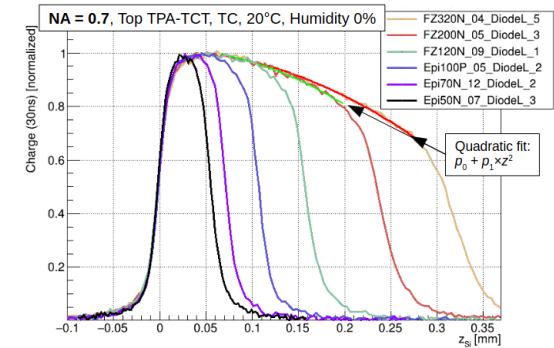


TPA-TCT measurements and simulations on CNM 8622 devices (illumination from top)

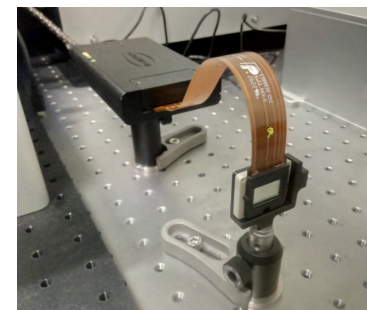
M. Moll, 43rd RD50 Workshop



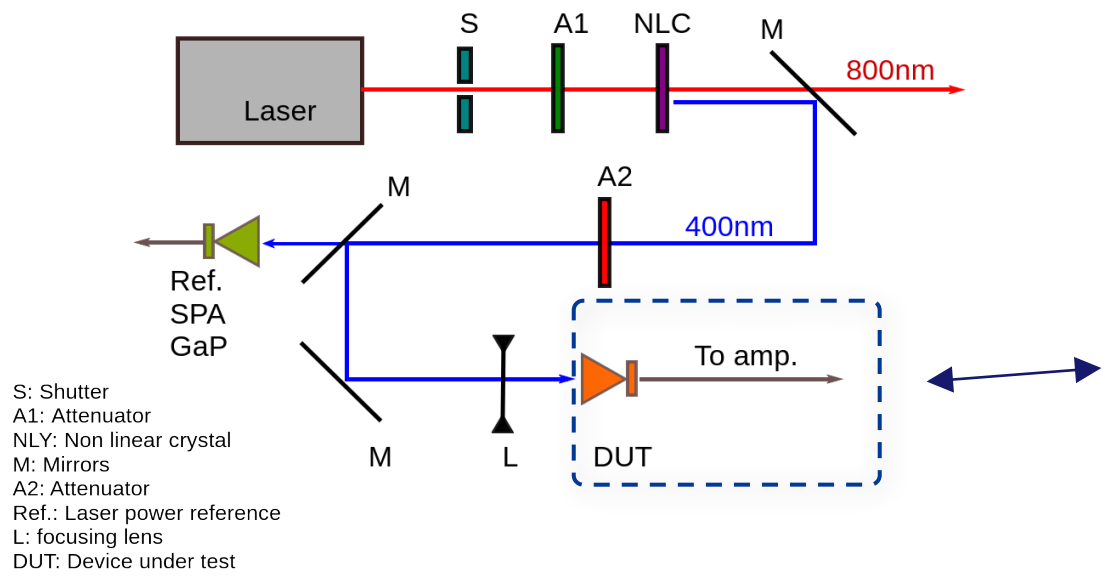
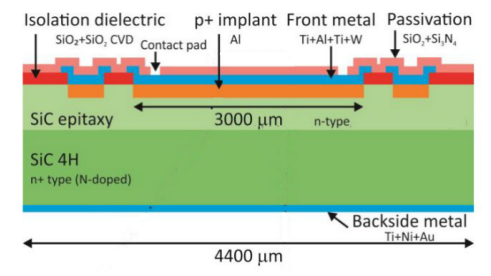
- Radiation hardness demands thin detectors, the longitudinal resolution in TPA is improved using objectives with  $NA > 0.5$  (=TPA baseline)
- Using highly focusing objectives ( $NA=0.7$ ) for thin devices, spherical aberration occurs
- Dynamic aberration correction via a Spatial Light Modulator (SLM)
- An applied voltage to a pixel changes it's refractive index:
  - The Phase front of the beam can be changed
  - In many applications in industry and science, micro-machining, microscopy, optical tweezers, etc., SLMs are used to improve the beam quality
- **Status at CERN SSD:**
  - Holoeye PLUTO-2.1-TELCO-142 Phase only LCOS SLM, 1920 x 1080 pixels,  $8\mu\text{m}$  pitch, 15.36mm x 8.64mm active area, 256 phase levels
  - Purchased and delivered
  - Commissioning started



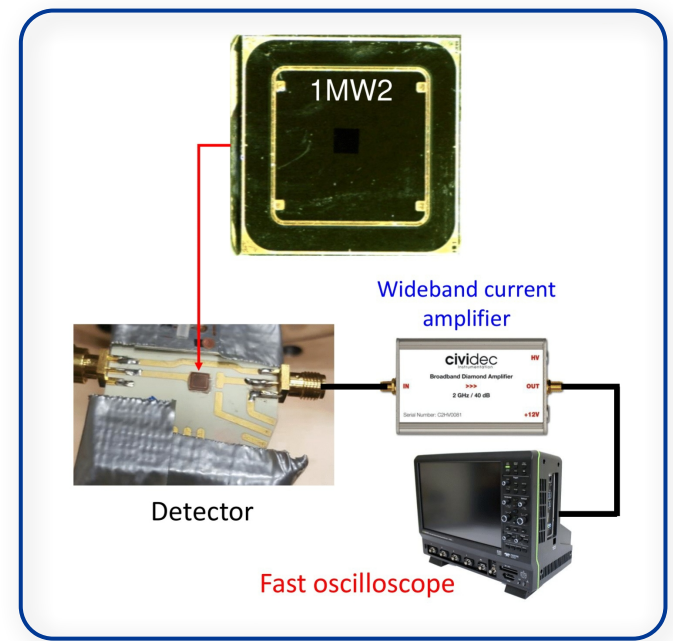
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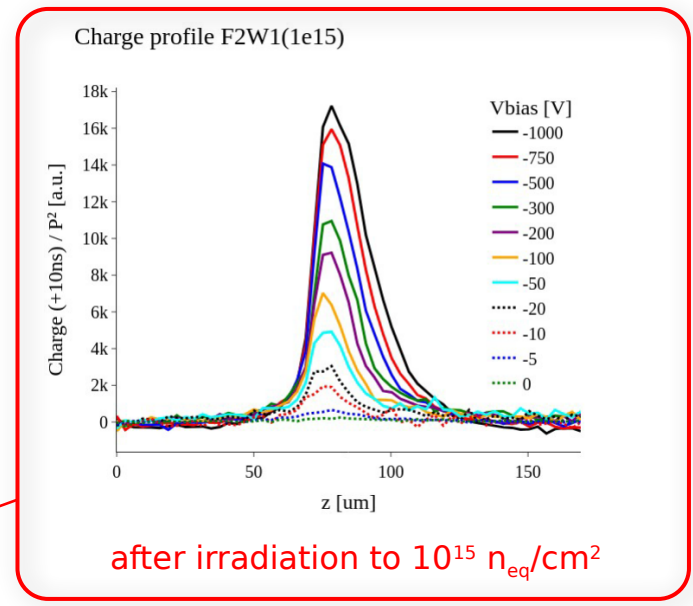
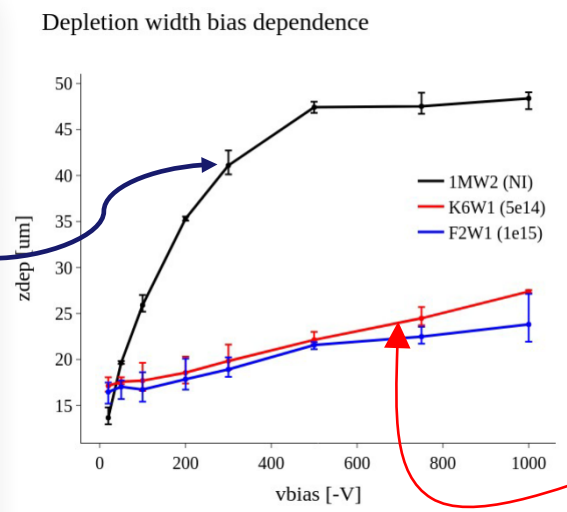
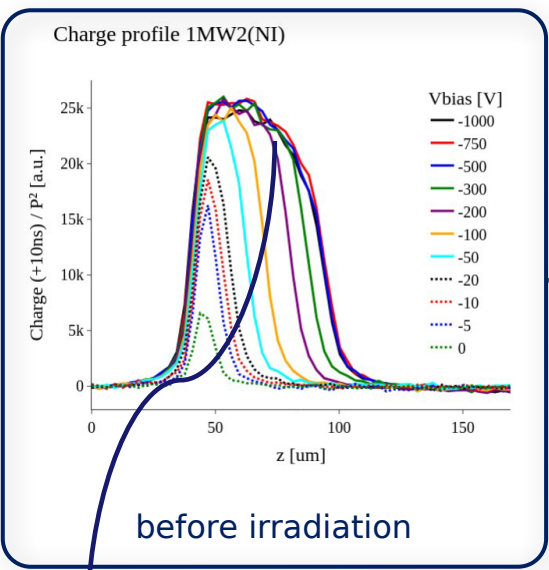
- Extension of TPA-TCT to other semiconductors
  - Si (1.12eV); **SiC (3.26eV)**; Diamond (5.46eV)
- SiC sensor study at UPV/EHU laser facility in Bilbao
  - Sensor: CNM planar p-in-n SiC epitaxial (50 $\mu$ m) sensor ( $N_{eff}=1.5e14cm^{-3}$ )



Readout for TPA-TCT



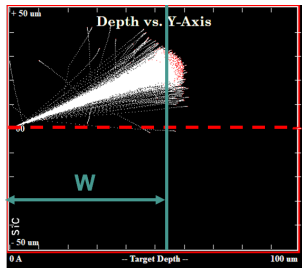
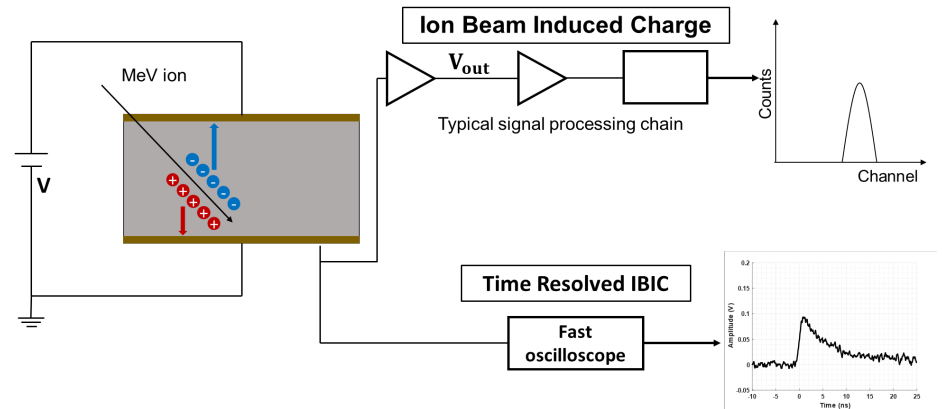
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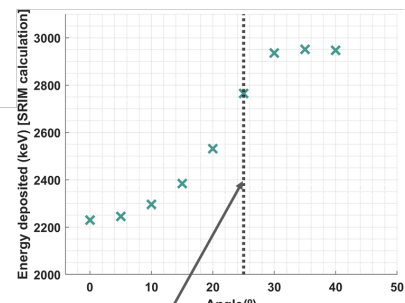
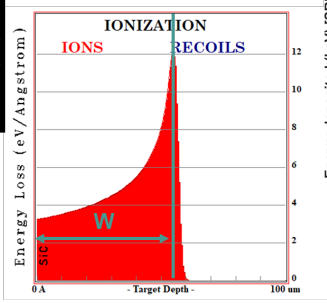
The in-depth charge profile was significantly influenced by **spherical aberration**. Specifically, the effect was more pronounced as the focal point became deeper.

Details: C.Quintana “**Update on the characterization of neutron irradiated IMB-CNM SiC planar diodes**”, presented on [41<sup>st</sup> RD50 Workshop](#), November 2022

- Validation of the experimental results using the **Ion Beam Induced Charge Method (IBIC)** measured at CNA in Seville (microprobe at Tandem)



$$E_{dep}(W, \theta) = \int_0^W \frac{dE}{dx}(\theta) dx$$



$$W[\mu m] = \text{Range}(E(\theta)) \times \cos(\theta)$$

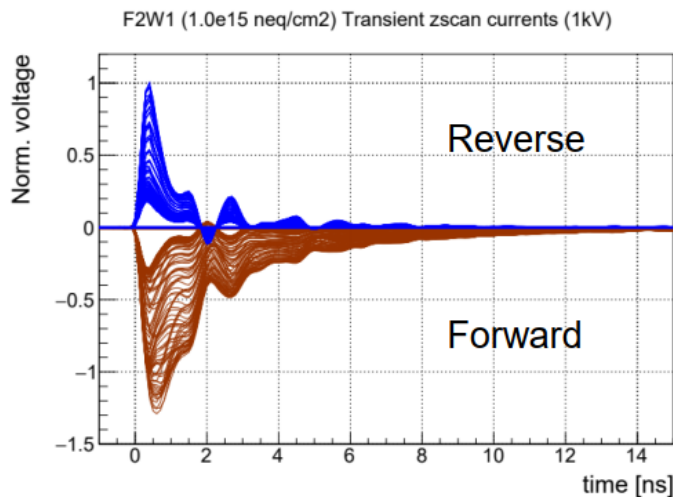
$\theta \rightarrow$  critical angle

Detector	Bias (V)	(W-IBIC±1) (μm)	W-TPA (μm)	W-CV (μm)
Pristine	350	46	43	39
	200	37	36	32
	100	27	27	23
$4 \times 10^{14} n_{eq}/cm^2$	800	20-25	25	45
	300	15-20	20	46
$1 \times 10^{15} n_{eq}/cm^2$	400	20-25	20	44
	200	15-20	17	44

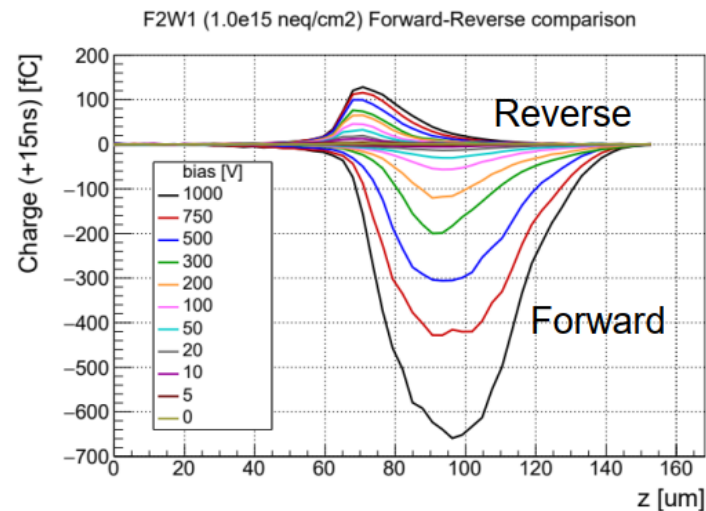
**Validation of the TPA results using the IBIC method!**

- SiC sensor study at UPV/EHU laser facility in Bilbao
  - Sensor: CNM planar p-in-n SiC epitaxial (50 $\mu$ m) sensor ( $N_{\text{eff}}=1.5\text{e}14\text{cm}^{-3}$ )

## Signal



## Charge profiles



### Interesting observations when forward biasing the irradiated diodes:

- Comparison between two z-scans at same HV bias but opposite polarization
- The signal amplitude is significantly greater in forward biasing than reverse biasing
- Large increase of the depletion width

Details: I Vila "Radiation Tolerance Study of neutron-irradiated SiC pn planar diodes", presented on TREDI 2023, Trento, March 2023

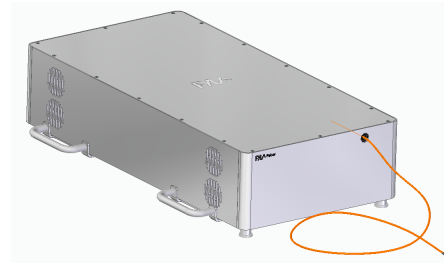
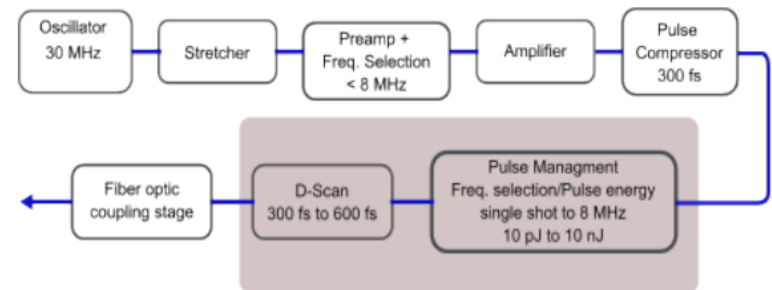


# Towards a new, more compact laser system

- Re-designed Laser system at Fyla – Status 2024
- The new “Pulsar” laser system was manufactured
  - The system fully integrates the laser pulse source (LPS), the pulse management module (LPM) and the dispersion compensation module (D-scan) in a single box component with fiber optic beam delivery.
  - The system “Pulsar” presents robustness and great stability in optical and temporal properties.
  - “Pulsar” provides beam delivery through 3m of optical fiber with coupling efficiency of ~70% (currently: under test and improvement)

### “Pulsar” system specifications

- **LPS:** Laser Pulse Source
  - All-fiber CPA femtosecond pulses generation
  - Pulse rep rate selection. **Single shot to 8MHz**
- **LPM:** Laser Pulse Management module
  - Pulse energy modulation: **10pJ to 10nJ**
  - Synchronized shutter, **rise/fall time < 1μs**
- **D-SCAN:** Dispersion scanning
  - Pulse duration tuning: **300fs to 600fs**
  - Pulse temporal properties characterization

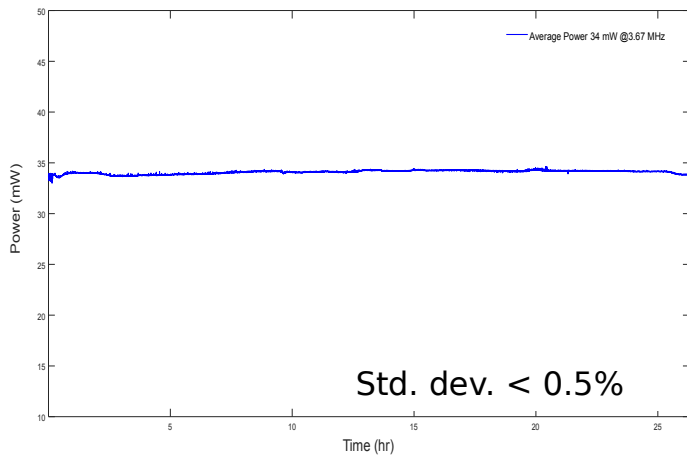


### **PULSAR** Dimensions:

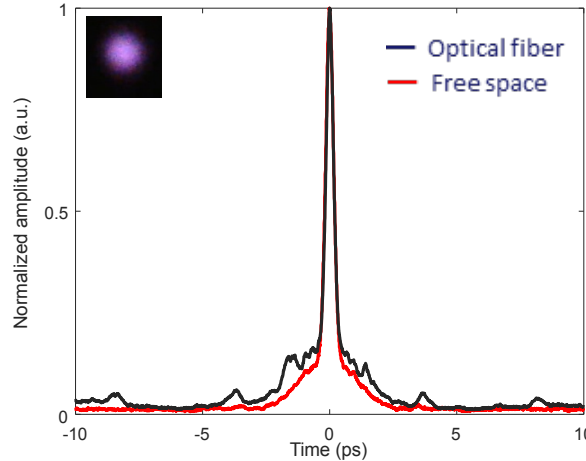
Length: 91 cm  
Width: 62 cm  
Height: 22 cm

- Testing the “Pulsar” laser performance

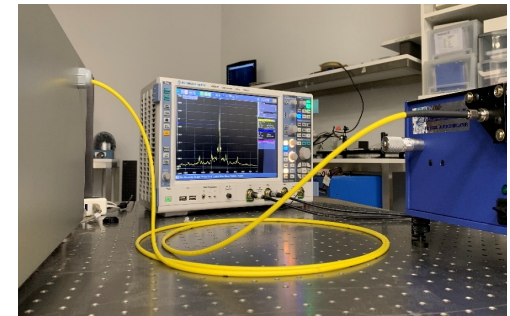
**Power stability**



**Pulse profile**



**Beam delivery**



Beam delivery through optical fiber, coupling efficiency ~70%

- Beam delivery through optical fiber (under test and improvement)
  - Coupling efficiency of ~ 70% to Kagome fiber under improvement
  - Studying new possibilities for beam delivery through optical fiber
- Difficulties with fiber beam delivery
  - Bending losses (20%)
  - Higher order (non-Gaussian) mode coupling when manipulating the output fiber

- **WP4.4 - Design & Development of a TPA-TCT Sensor Characterization System**
  - **Scope:** Development of a customizable and user friendly Two Photon Absorption – Transient Current Technique (TPA-TCT) system for the characterization and testing of silicon devices
  - **Beneficiaries:** CERN (task leader); CSIC-IFCA (Santander, ES); Fyla (Valencia, ES)
  - **Deliverables/Milestones:**
    - MS16 (M23–February 2023) – Commissioning of complete TPA-TCT system [**Done**]  
Milestone Document report: <https://zenodo.org/records/8027093>
    - D4.4. (M46–January 2025) Publications & systems operational at several institutes [**Well on track**]
- **Status March 2024:**
  - **Laser systems:**
    - Fyla LFC1500X at CERN, IFCA (ES), JSI Ljubljana (SI), NIKHEF (NL), Lancaster (UK)
    - Fyla “Pulsar” in setup phase at Oxford (UK)
  - **Work of last 12 months:** see publication list in Annex
  - **New compact laser system developments:**
    - 2023: Work started at Fyla on new design
    - 2024: System “Pulsar” presents robustness and great stability in optical and temporal properties; beam delivery through 3m of optical fiber with coupling efficiency of ~70%
  - **User community:**
    - TPA-TCT lasers have been delivered to 6 HEP institutes; CERN/IFCA/Fyla provided consulting for setting up the systems
    - TPA-TCT common effort presented as example for collaborative efforts for new R&D collaboration (DRD3) in ECFA Detector R&D roadmap implementation plan.

# Annex

• Objectives:

**Task 4.4 Design & development of a new sensor characterisation system based on the TPA-TCT technique**

- Complete the development from the proof-of-concept installation towards a customisable user friendly Two-Photon Absorption (TPA) Transient Current Technique (TCT) system with data acquisition and data analysis tools
- Support the evaluation of newly developed sensors (Low-Gain Avalanche Detectors and depleted CMOS devices) developed in WP5 and WP6
- Offer support towards the implementation of similar systems in other European institutions

• Description of work:

**Task 4.4 Design & Development of a New Sensor Characterisation System based on TPA-TCT Technique (CERN, CSIC-IFCA, FYLA)**

The Transient Current Technique (TCT) as a tool for studying signal formation in solid-state detectors is limited in resolution and allows for two-dimensional scans only. Two-Photon Absorption (TPA) TCT overcomes this limitation by employing a femtosecond laser pulse that creates charges only in a tiny voxel in the focal point of the laser beam, allowing, for example, small volume pixel detectors. This task will thus develop a novel very powerful tool for precise characterisation of semiconductor devices and offer it to the community for testing newly developed sensor technologies. FYLA will improve the performance and usability of the fiber laser for the TPA-TCT by increasing the laser stability and using a new fibre-based beam delivery system.

• 1 Milestone:

MS4.5	Commission a complete TPA-TCT system	4.4	M23	Report
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• 1 Deliverable:

<b>D4.4: Support towards the implementation of TPA-TCT systems and contribute to the evaluation of newly developed sensors technologies</b> <i>Publication on TPA-TCT evaluation of sensors (task 4.4)</i>	46
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**January 2025**

AIDAinnova publications (task 4.4.):

- **Influence of temperature on measurements of the Two Photon Absorption - Transient Current Technique in silicon planar detectors using a 1550 nm femtosecond fibre laser;** *S. Pape, E.Currás, M.Fernández García, M. Moll, M. Wiehe*, Nuclear Instruments and Methods in Physics Research Section A: Accelerators Spectrometers Detectors and Associated Equipment, Volume 1053, August 2023, 168387; <https://doi.org/10.1016/j.nima.2023.168387>
- **Technique for the investigation of segmented sensors using the Two Photon Absorption - Transient Current Technique;** *Sebastian Pape, Esteban Currás, Marcos Fernández García, Michael Moll*; Sensors 2023, 23(2), 962; <https://doi.org/10.3390/s23020962>
- **Fiber Laser System of 1550 nm Femtosecond Pulses with Configurable Properties for the Two-Photon Excitation of Transient Currents in Semiconductor Detectors;** *Azahara Almagro-Ruiz, Sebastian Pape, Hector Muñoz, Moritz Wiehe, Esteban Curras Rivera, Marcos Fernández-García, Michael Moll, Raúl Montero Santos, Rogelio Palomo, Cristian Quintana, Iván Vila Álvarez, Pere Pérez-Millán*; Applied Optics 61, 9386-9397 (2022); <https://doi.org/10.1364/AO.470780>
- **Characterisation of irradiated and non-irradiated silicon sensors with a table-top Two Photon Absorption TCT system;** *S. Pape, M. Fernández García, M.Moll, R. Montero, F.R. Palomo, I. Vila and M. Wiehe*; Journal of Instrumentation, C08011, 2022, volume 17, number 08; <https://doi.org/10.1088/1748-0221/17/08/c08011>
- **Plasma effects in silicon detectors and the Two Photon Absorption Transient Current Technique;** *F.R. Palomo, M. Moll, M. Fernández-García, R. Montero, I. Vila*; Proceedings of the 2021 21th European Conference on Radiation and Its Effects on Components and Systems (RADECS) <https://doi.org/10.1109/RADECS53308.2021.9954488>
- **Development of a Tabletop Setup for the Transient Current Technique Using Two Photon Absorption in Silicon Particle Detectors;** *Moritz Wiehe, Marcos Fernández García, Michael Moll, Raúl Montero, F.R.Palomo, Ivan Vila, Héctor Muñoz-Marco, Viorel Otgon, Pere Pérez-Millán*; IEEE TNS, Vol.68, Issue.2, Feb.2021, pages 220-228, <https://doi.org/10.1109/TNS.2020.3044489>
- **First observation of the charge carrier density related gain reduction mechanism in LGADs with the Two Photon Absorption - Transient Current Technique;** *S.Pape, E.Currás, M.Fernández García, M.Moll,R.Montero, F.R.Palomo, I.Vila, M.Wiehe, C.Quintana*; July 2022; Nuclear Instruments and Methods in Physics Research Section A Accelerators Spectrometers Detectors and Associated Equipment 1040:167190; <https://doi.org/10.1016/j.nima.2022.167190>